



ELECTRONICS, INC.

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## NTE2636 Silicon NPN Transistor Horizontal Deflection <sup>w</sup>/Internal Damper Diode

### Features:

- High Breakdown Voltage:  $V_{CES} = 1500V$
- Built-In Damper Diode
- Isolated TO3PFM Type Package

### Applications:

- TV/Character Display Horizontal Deflection Output

### Absolute Maximum Ratings: ( $T_A = +25^\circ C$ unless otherwise specified)

Collector–Emitter Voltage, $V_{CES}$ .....	1500V
Emitter–Base Voltage, $V_{EBO}$ .....	6V
Collector Current, $I_C$ .....	8A
Collector Peak Current, $I_{C(peak)}$ .....	9A
Collector Surge Current, $I_{C(surge)}$ .....	18A
Collector–Emitter Diode Forward Current, $I_D$ .....	8A
Collector Power Dissipation ( $T_C = +25^\circ C$ ), $P_C$ .....	50W
Operating Junction Temperature, $T_J$ .....	+150°C
Storage Temperature Range, $T_{stg}$ .....	-55° to +150°C

### Electrical Characteristics: ( $T_A = +25^\circ C$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Emitter–Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 500mA, I_C = 0$	6	–	–	V
Collector Cutoff Current	$I_{CES}$	$V_{CE} = 1500V, R_{BE} = 0$	–	–	500	$\mu A$
DC Current Transfer Ratio	$h_{FE}$	$V_{CE} = 5V, I_C = 1A$	–	–	25	
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 6A, I_B = 1.2A$	–	–	5	V
Base–Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 6A, I_B = 1.2A$	–	–	1.5	V
Collector–Emitter Diode Forward Voltage	$V_{ECF}$	$I_F = 8A$	–	–	2.0	V
Fall Time	$t_f$	$I_{CP} = 6A, I_{B1} = 1.2A, I_{B2} \cong -2.4A,$ $f_H = 31.5kHz$	–	–	0.5	$\mu s$

